

March 23, 2017
Memory Q & R Engineering Department
Memory Division
Storage & Electronic Devices Solutions Company
TOSHIBA CORPORATION

To: _____

**Subject: Notification of Wire Material Change for
24nm Serial NAND with WSON Package**

This is to notify the wire material of Serial NAND will be changed as follows.

1. AFFECTED PRODUCTS

24nm Serial NAND with WSON package

1Gbit	1.8V	TC58CYG0S3HRAIG
1Gbit	3.3V	TC58CVG0S3HRAIG
2Gbit	1.8V	TC58CYG1S3HRAIG
2Gbit	3.3V	TC58CVG1S3HRAIG
4Gbit	1.8V	TC58CYG2S0HRAIG
4Gbit	3.3V	TC58CVG2S0HRAIG

2. REASON FOR CHANGE

The existing gold (Au) wire will be changed to copper (Cu) wire in order to improve production efficiency, the Cu wire has been used on our other products with verified quality and reliability.

3. IMPLEMENTATION DATE

From July 2017(delivery base)
Customer evaluation samples are available upon request.

4. RELIABILITY TEST RESULTS

Samples passed the following reliability tests.

Test	Conditions	Pass/SS Judge
Adhesive Test	30°C/70% RH/192h + Reflow (260°C x 4 times)	60pcs/60pcs Pass
HAST	130°C/85% RH, 100h	100pcs/100pcs Pass
TCT	-65°C/150°C, 500cyc	100pcs/100pcs Pass

5. IDENTIFICATION

The new products will be identified by a different additional code (ADDC) on barcode label affixed on an outer carton as shown below.

	Wire material	ADDC
Tray	Au Wire (before change)	BA H
	Cu wire (after change)	BA J
Embossed taping	Au Wire (before change)	BA 0
	Cu wire (after change)	BA 1

6. CUSTOMER ACKNOWLEDGEMENT OF RECEIPT

If customers have any questions on this change, please contact our sales representatives.
No acknowledgement or response will be considered that this change has been accepted.

Sincerely,



Kazuo Hatakeyama
Group Manager
Memory Customer & Engineering Group
Memory Q & R Engineering Department
Storage & Electronic Devices Solutions Company
TOSHIBA Corporation